
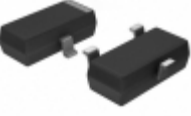







	<h2>SI3417DV-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI3417DV-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 30V 8A TSOP-6</p> <p>Datenblätter:  SI3417DV-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 46100 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI3417DV-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 30V 8A TSOP-6
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	46100 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-23-6 Thin, TSOT-23-6
Supplier Device-Gehäuse	6-TSOP
Verlustleistung (max)	2W (Ta), 4.2W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A (Ta)
Rds On (Max) @ Id, Vgs	25.2 mOhm @ 7.3A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	50nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1350pF @ 15V
Verpackung	Tape & Reel (TR)



















































SI3417DV-T1-GE3 ist neu im Original, Suche SI3417DV-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI3417DV-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI3417DV-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI3415A-TP Micro Commercial Components (MCC) P-CHANNEL, MOSFETS, SOT-23 PACKAGE</p>	 <p>SI3417DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 8A TSOP-6</p>	 <p>SI3421DV-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 8A TSOP-6</p>	 <p>SI3420-TP Micro Commercial Components (MCC) MOSFET N-CHANNEL 20V 6A SOT23</p>
 <p>SI3415-TP Micro Commercial Components (MCC) MOSFET P-CH 20V 4A SOT-23</p>	 <p>SI3420A-TP Micro Commercial Components (MCC) MOSFET N-CH 20V 6A SOT-23</p>	 <p>SI3421DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 8A TSOP-6</p>	 <p>SI3410DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 8A 6-TSOP</p>

heiße Teile

Mehr

 SI3239-FM	 SI3239-GM	 SI3239-ZM3	 SI32391-B-FM	 SI32392-B-FM
 SI32392-B-FMR	 SI32392-FM	 SI3240CS	 SI3241-D-FQR	 SI3241-FQ
 SI3241-GQ	 SI32919-A-FS	 SI32919-A-FSR	 SI32919A-FSR	 SI3402-A-GMR
 SI3402-GM	 SI3403DV-T1-GE3	 SI3407DV-T1-E3	 SI3407DV-T1-E3	 SI3407DV-T1-GE3
 SI3407DV-T1-GE3	 SI3410DV-T1-E3	 SI3410DV-T1-E3	 SI3410DV-T1-GE3	 SI3410DV-T1-GE3
 SI3417DV-T1-GE3	 SI3420DV-T1-GE3	 SI3421DV-T1-GE3	 SI3421DV-T1-GE3	 SI3422DV
 SI3422DV-T1	 SI3422DV-T1-GE3	 SI3424BDV	 SI3424BDV-T1-E3	 SI3424BDV-T1-E3
 SI3424BDV-T1-GE3	 SI3424BDV-T1-GE3	 SI3424CDV	 SI3424CDV-T1-E3	 SI3424CDV-T1-GE3
 SI3424CDV-T1-GE3	 SI3424DV-T1	 SI3424DV-T1-E3	 SI3424DV-T1-E3	 SI3424DV-T1-GE3
 SI3424DV-T1-GE3	 SI3424DV-TI-E3	 SI3425DV	 SI3429EDV-T1-GE3	 SI3429EDV-T1-GE3

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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